TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SA1943

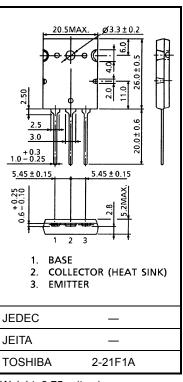
Power Amplifier Applications

• High collector voltage: VCEO = -230 V (min)

- Complementary to 2SC5200
- Recommended for 100-W high-fidelity audio frequency amplifier output stage.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	-230	V	
Collector-emitter voltage	V _{CEO}	-230	V	
Emitter-base voltage	V _{EBO}	-5	V	
Collector current	Ι _C	-15	А	
Base current	Ι _Β	-1.5	А	
Collector power dissipation (Tc = 25°C)	P _C	150	W	
Junction temperature	Тј	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	



Weight: 9.75 g (typ.)

Electrical Characteristics (Ta = 25°C)

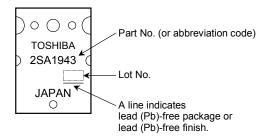
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -230 \text{ V}, I_{E} = 0$	_	_	-5.0	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = -5 V, I_C = 0$	_	_	-5.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	$I_{\rm C}$ = -50 mA, $I_{\rm B}$ = 0	-230			V
DC current gain	h _{FE (1)} (Note)	V _{CE} = -5 V, I _C = -1 A	55	-	160	
	h _{FE (2)}	$V_{CE} = -5 V, I_C = -7 A$	35	60	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -8 A, I _B = -0.8 A	_	-1.5	-3.0	V
Base-emitter voltage	V _{BE}	$V_{CE} = -5 V, I_C = -7 A$	_	-1.0	-1.5	V
Transition frequency	f _T	V _{CE} = -5 V, I _C = -1 A	_	30	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	-	360	_	pF

Note: hFE (1) classification R: 55 to 110, O: 80 to 160

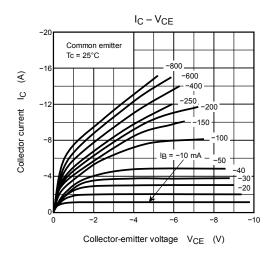
Unit: mm

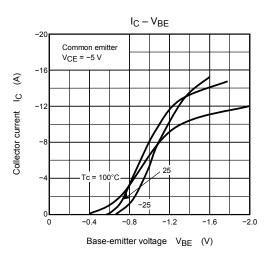
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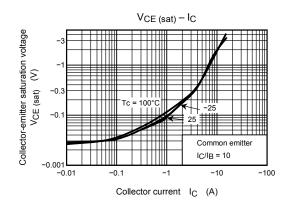
Marking

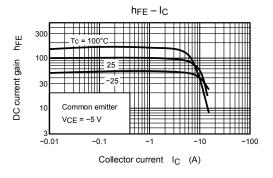


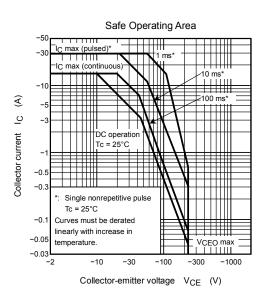
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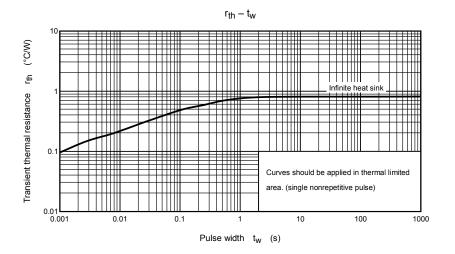












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